

**LATERAL FIELD-EFFECT-CONTROLLABLE SEMICONDUCTOR
COMPONENT FOR RF APPLICATIONS**

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Abstract

The present invention relates to a semiconductor component. The component includes a semiconductor body with a first semiconductor layer of a first conduction type and a second semiconductor layer of a second conduction type. The component includes, in the second semiconductor layer, a first terminal zone of the second conduction type, a drift zone of the second conduction type, a channel zone of the first conduction type, which is formed between the first terminal zone and the drift zone, and a second terminal zone of the second conduction type, which is arranged at a distance from the channel zone in the lateral direction of the semiconductor body. The component also includes a first drive electrode and at least one second drive electrode.

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